IN THE CLAIMS:

Kindly amend claims 1-4, cancel claims 5-7 without prejudice or admission, and add new claims 8-16 as shown in the following listing of claims, which replaces all previous versions and listings of claims in this application.

1. (currently amended) A semiconductor device comprising:

a semiconductor substrate having a first conductivity type;

a field oxide film ~~formed~~ disposed on ~~a~~ the semiconductor substrate ~~of one conductivity type~~;

a gate electrode surrounded by the field oxide film and disposed ~~formed through a gate oxide film~~ on the semiconductor substrate through a gate oxide film; ~~of one conductivity type, which is surrounded by the field insulation film;~~

a low concentration source/drain region ~~of a reverse conductivity type formed~~ disposed in a region over the semiconductor substrate surrounded by the field oxide film and the gate electrode, the low concentration source/drain region having a second conductivity type opposite to the first conductivity type;

an interlayer film disposed over the semiconductor substrate for electrically isolating the gate electrode and the low concentration source/drain region ~~of the reverse conductivity type from a wiring formed thereon~~ from wirings disposed on the interlayer film;

a plurality of etched contact ~~hole formed in~~ holes extending through the interlayer film for electrically connecting ~~between the wiring, and~~ the gate electrode and the low concentration source/drain region ~~of the reverse conductivity type~~ with the wirings disposed on the interlayer film;

a nitride film ~~formed~~ disposed under the interlayer film for preventing the semiconductor substrate ~~of one conductivity type~~ from being overetched ~~when forming~~ during formation of the etched contact ~~hole~~ holes in the interlayer film; and

a plurality of high concentration diffusion layers having the second conductivity type and disposed ~~layer of a reverse conductivity type selectively formed~~ only in respective portions of the low concentration source/drain region directly under the respective contact holes. ~~of the reverse conductivity type where the contact hole is formed.~~

2. (currently amended) A semiconductor device according to ~~claim 1, wherein~~ claim 1; wherein the low concentration source/drain region ~~of the reverse conductivity type~~ has an impurity concentration of $1x10^{16}$ to $1x10^{18}$ atoms/cm^3.

3. (currently amended) A semiconductor device according to ~~claim 1, wherein~~ claim 1; wherein each of the high concentration diffusion ~~layer of the reverse conductivity type~~ layers has an impurity concentration of $1x10^{19}$ to $5x10^{20}$ atoms/cm^3.

4. (currently amended) A semiconductor device according to ~~claim 1, wherein~~ claim 1; wherein the nitride film has a film thickness of 100 to 500 Å.

5. - 7.(canceled).

8. (new) A semiconductor device according to claim 1; wherein the interlayer film comprises a BPSG interlayer film.

9. (new) A semiconductor device comprising:

a semiconductor substrate having a first conductivity type;

a gate insulating film disposed on a surface of the semiconductor substrate;

a gate electrode disposed on the gate insulating film;

a plurality of low concentration diffusion layers disposed on the surface of the semiconductor substrate on opposite sides of the gate electrode, the low concentration diffusion layers having a second conductivity type different from the first conductivity type;

an interlayer film disposed over the semiconductor substrate for electrically isolating the gate electrode and the low concentration diffusion layers from wiring disposed on the interlayer film;

a plurality of contact holes extending through the interlayer film for electrically connecting the gate electrode and the low concentration diffusion layers with the wirings disposed on the interlayer film; and

a plurality of high concentration diffusion layers having the second conductivity type and disposed only in portions of the respective low concentration diffusion layers directly under the respective contact holes.

10. (new) A semiconductor device according to claim 9; wherein the contact holes comprise etched contact holes; and further comprising an etch-stop film disposed under the interlayer film for preventing the semiconductor substrate from being overetched during formation of the etched contact holes in the interlayer film.

11. (new) A semiconductor device according to claim 10; wherein the etch-stop film has a film thickness of 100 to 500 Å.

12. (new) A semiconductor substrate according to claim 10; wherein the etch-stop film comprises a nitride film.

13. (new) A semiconductor device according to claim 12; wherein the nitride film has a film thickness of 100 to 500 Å.

14. (new) A semiconductor device according to claim 9; wherein each of the low concentration diffusion layers has an impurity concentration of $1x10^{16}$ to $1x10^{18}$ atoms/cm^3.

15. (new) A semiconductor device according to claim 9; wherein each of the high concentration diffusion layers has an impurity concentration of $1x10^{19}$ to $5x10^{20}$ atoms/cm^3.

16. (new) A semiconductor device according to claim 9; wherein the interlayer film comprises a BPSG interlayer film.